

VS-VSKT320PbF

Vishay Semiconductors

Thyristor/Thyristor (MAGN-A-PAK Power Modules), 320 A



M	AG	N-	Α-	PΑ	K

PRIMARY CHARACTERISTICS					
I _{T(AV)}	320 A				
Туре	Modules - thyristor, standard				
Package	MAGN-A-PAK				

FEATURES

- High voltage
- · Electrically isolated base plate
- 3600 V_{RMS} isolating voltage
- · Industrial standard package
- · Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION

This VSK series of MAGN-A-PAK modules uses high voltage power thyristor/thyristor in doubler circuit configuration. The semiconductors are electrically isolated from the metal base, allowing common heatsinks and compact assemblies to be built. They can be interconnected to form single phase or three phase bridges or as AC-switches when modules are connected in anti-parallel mode. These modules are intended for general purpose applications such as battery chargers, welders, motor drives, UPS, etc.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
I _{T(AV)}	70 °C	320					
I _{T(RMS)}		710					
Ітѕм	50 Hz	9000	A				
	60 Hz	9420					
l ² t	50 Hz	405	1.42-				
1-1	60 Hz	370	kA ² s				
I²√t		4050	kA ^{2√} s				
V _{DRM} /V _{RRM}		1200 to 1600	V				
T _J	Range	-40 to +130	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND OFF-STATE BLOCKING VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 130 °C MAXIMUM mA				
VS-VSKT320-	12	1200	1300	50				
VS-VSK1320- 16		1600	1700	30				



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PARAMETER	SYMBOL	-	TEST CONDITIO	NS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	180° conduction	180° conduction, half sine wave			Α
at case temperature	.()				70	°C
Maximum RMS on-state current	I _{T(RMS)}	As AC switch			710	
		t = 10 ms	No voltage		9000	
Maximum peak, one-cycle on-state		t = 8.3 ms	reapplied		9420	А
non-repetitive, surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}]	7570	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	7920	
		t = 10 ms	No voltage	initial T _J =	405	kA ² s
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied	T _J maximum -	370	
		t = 10 ms	100 % V _{RRM} reapplied		287	
		t = 8.3 ms			262	
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10	ms, no voltage re	applied	4050	kA²√s
Low level value or threshold voltage	V _{T(TO)1}		(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T _{.I} = T _{.I} maximum			V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J$	_J = T _J maximum		1.03	
Low level value on-state slope resistance	r _{t1}	(16.7 % x π x I _{T(} T _J = T _J maximus	$_{(AV)} < I < \pi \times I_{T(AV)},$ m		0.75	mΩ
High level value on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.53	11152
Maximum peak on-state or	V V	$I_{TM} = 750 \text{ A}, T_J = 25 \text{ °C}, 180 \text{ ° conduction},$ average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$			1.40	V
forward voltage drop	$V_{TM}, V_{FM},$	$I_{TM} = 750 \text{ A}$, $T_J = T_J \text{ maximum}$, 180° conduction, average power = $V_{T(TO)} \times I_{T(AV)} + r_f \times (I_{T(RMS)})^2$			1.37	V
Maximum holding current	I _H		12 V, initial $I_T = 3$		500	
Maximum latching current	ΙL		12 V, resistive loa /, 100 μ s, T _J = 25	1000	mA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical delay time	t _d	T _J = 25 °C, gate current = 1 A dl _α /dt = 1 A/μs	1.0					
Typical rise time	t _r	$V_{d} = 0.67 \% V_{DRM}$	2.0	μs				
Typical turn-off time range	t _q	I_{TM} = 300 A; dI/dt = 15 A/ μ s; T_J = T_J maximum; V_R = 50 V; dV/dt = 20 V/ μ s; gate 0 V, 100 Ω	200 to 350					

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak reverse and off-state leakage current	I _{RRM,} I _{DRM}	$T_J = T_J \text{ maximum}$	50	mA			
RMS insulation voltage	V _{INS}	50 Hz, circuit to base, all terminals shorted, 25 $^{\circ}\text{C}$, 1 s	3600	V			
Critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, exponential to 67 % rated V_{DRM}	1000	V/µs			



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TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum peak gate power	P _{GM}	$t_p \le 5 \text{ ms}, T_J = T_J r$	maximum	10.0	W	
Maximum average gate power	P _{G(AV)}	$f = 50 \text{ Hz}, T_J = T_J \text{ r}$	maximum	2.0	VV	
Maximum peak gate current	+ I _{GM}	$t_p \le 5 \text{ ms}, T_J = T_J r$	maximum	3.0	А	
Maximum peak negative gate voltage	- V _{GT}	$t_p \le 5 \text{ ms}, T_J = T_J r$	maximum	5.0	V	
		T _J = - 40 °C	Anode supply = 12 V, resistive load; Ra = 1 Ω	4.0		
Maximum required DC gate voltage to trigger	V _{GT}	T _J = 25 °C		3.0		
		T _J = T _J maximum		2.0		
		T _J = - 40 °C	Anode supply = 12 V, resistive load; Ra = 1 Ω	350	mA	
Maximum required DC gate current to trigger	I_{GT}	T _J = 25 °C		200		
		T _J = T _J maximum	, , , , , , , , , , , , , , , , , , ,	100		
Maximum gate voltage that will not trigger	V_{GD}	$T_J = T_J$ maximum, rated V_{DRM} applied		0.25	V	
Maximum gate current that will not trigger	I _{GD}	$T_J = T_J$ maximum, rated V_{DRM} applied		10.0	mA	
Maximum rate of rise of turned-on current	dl/dt	$T_J = T_J$ maximum, rated V_{DRM} applied		500	A/μs	

THERMAL	THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	ł	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Junction operating and storage temperature range		T _J , T _{Stg}		-40 to +130	°C		
Maximum thermal resistance, junction to case per junction		R _{thJC}	DC operation	0.125	K/W		
	ical thermal resistance, e to heatsink per module		Mounting surface flat, smooth and greased	0.02	I ⊘ VV		
Mounting torque	MAGN-A-PAK to heatsink		A mounting compound is recommended and the torque should be rechecked after	4 to 6	Nm		
± 10 %	busbar to MAGN-A-PAK		a period of about 3 hours to allow for the spread of the compound.	4 10 0	NIII		
Approximate	woight			500	g		
Approximate	weigni			17.8	OZ.		
Case style				MAGN	-A-PAK		

△R CONDUCTION PER JUNCTION											
DEVICES	SINUS	SINUSOIDAL CONDUCTION AT T _J MAXIMUM RECTANGULAR CONDUCTION AT T _J MAXIMUM					UNITS				
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSKT320-	0.009	0.010	0.013	0.020	0.032	0.007	0.011	0.015	0.020	0.033	K/W

Note

• Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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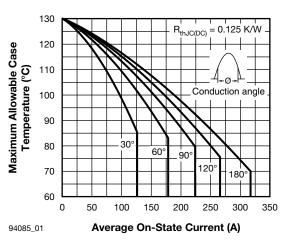


Fig. 1 - Current Ratings Characteristics

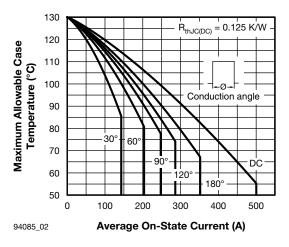


Fig. 2 - Current Ratings Characteristics

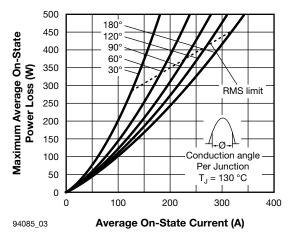


Fig. 3 - On-State Power Loss Characteristics

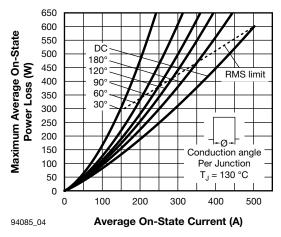


Fig. 4 - On-State Power Loss Characteristics

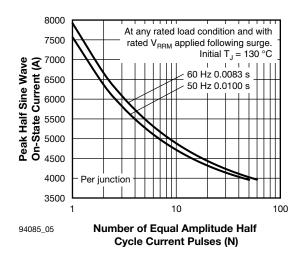


Fig. 5 - Maximum Non-Repetitive Surge Current

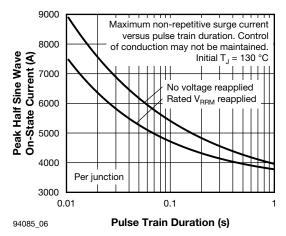


Fig. 6 - Maximum Non-Repetitive Surge Current

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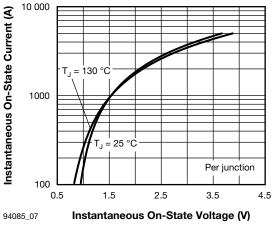


Fig. 7 - On-State Voltage Drop Characteristics

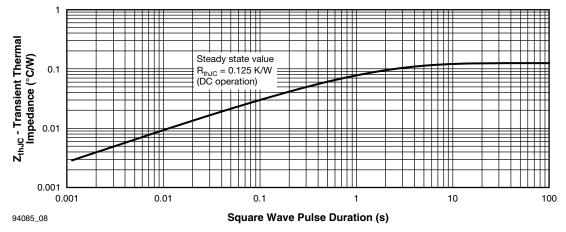
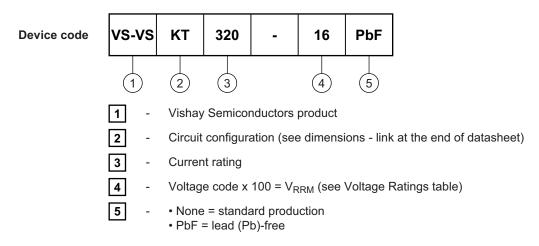


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE



Note

• To order the optional hardware go to www.vishay.com/doc?95172

End of Life December 2024 - Contact Vishay for Alternative Solutions



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CIRCUIT CONFIGURATION					
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
Two SCRs doubler circuit	КТ	0 -			

LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95086



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